

# **ECENCAB5VBH**

**E**core

Low-Capacitance Bidirectional Micro Packaged TVS Diodes for ESD Protection

The ECENCAB5VBH is designed with ECORE Punch-Through process TVS technology to protect voltage sensitive components from ESD. Excellent clamping capability, low leakage, and fast response time provide best in class protection on designs that are exposed to ESD. Because of its small size, it is suited for use in cellular phones, MP3 players, digital cameras and many other portable applications where board space comes at a premium.

This series has been specifically designed to protect sensitive components which are connected to data and transmission lines from overvoltage caused by ESD(electrostatic discharge), and EFT (electrical fast transients).

### Features

- Peak Power Dissipation –65 W (8 x 20 us Waveform)
- Stand-off Voltage: 5.0 V
- Low capacitance for high-speed interfaces
- Replacement for MLV (0402)
- Protects I/O、 VCC Port
- Low Clamping Voltage
- Low Leakage
- Low Capacitance
- Response Time is < 1 ns
- Meets MSL 1 Requirements
- ROHS compliant

## **Main applications**

- Serial and Parallel Ports
- Notebooks, Desktops, Servers
- Projection TV
- Cellular handsets and accessories
- Portable instrumentation
- Peripherals

### **Protection solution to meet**

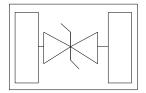
IEC61000-4-2 (ESD) ±20kV (air), ±20kV (contact)

### **Ordering Information**

Device	Marking	Qty per Reel	Reel Size
ECENCAB5VBH	PB	10000pcs	7inch



**DFN1006** 





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Maximum ratings (rand-25 C Oness Otherwise Specified)				
Parameter	Symbol	Value	Unit	
Peak Pulse Power (tp=8/20µs waveform)	Рррр	65	Watts	
Peak pulse current (tp=8/20µs waveform)	$I_{PP}$	6	А	
ESD Rating per IEC61000-4-2: Contact		20	KV	
Air		20	ΚV	
Lead Soldering Temperature	TL	260 (10 sec.)	°C	
Operating Temperature Range	ΤJ	-55 ~ 150	°C	
Storage Temperature Range	Tstg	-55 ~ 150	°C	

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

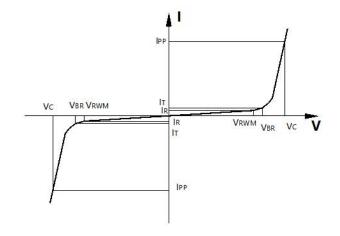
\*Other voltages may be available upon request.

1. Non-repetitive current pulse, per Figure 1.

Electric	Electrical characteristics (Tamb=25°C Unless Otherwise Specified)					
Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
Vrwm	Reverse Working Voltage				5	V
VBR	Reverse Breakdown Voltage	$I_T = 1 m A$ ,	5.8		9.5	V
Ir	Reverse Leakage Current	$V_{RWM} = 5V,$			0.5	μΑ
Vc	Clamping Voltage	$I_{PP} = 6A$ , tp =8/20µs,		9	12	V
CJ	Junction Capacitance	$V_{R} = 1V, f = 1MHz,$		13	19	pF

Junction capacitance is measured in  $V_R=0V$ ,F=1MHz

Symbol	Parameter	
Vrwm	Working Peak Reverse Voltage	
VBR	Breakdown Voltage @ I <sub>T</sub>	
Vc	Clamping Voltage @ IPP	
I <sub>T</sub>	Test Current	
Irm	Leakage current at VRWM	
Ірр	Peak pulse current	
Co	Off-state Capacitance	
CJ	Junction Capacitance	





# ECENCAB5VBH

#### Typical electrical characterist applications Waveform Peak Pulse Power-P<sub>PK</sub> (KW) Parameters: tr=8us Ш Percent of IPP td=20us 0.1 Ϊ td=IPP/2 0 0.01 0.1 Pulse Duration-tp (us) Time (us) Non-Repetitive Peak Pulse Power vs. Pulse Time **Pulse Waveform** % of Rated Power or Ipp 10 Ambient Temperature-T A (°C) **Power Derating Curve**



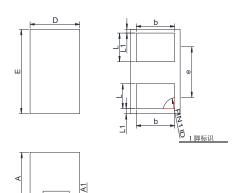
# **Package Information**

### **DFN1006**

# Mechanical Data

Case:DFN1006

Case Material: Molded Plastic. UL Flammability



DIM	Millimeters		
DIM	Min	Max	
Α	0.40	0.50	
A1	0.00	0.05	
D	0.55	0.65	
Е	0.95	1.05	
b	0.45	0.55	
e	0.65TYP		
L	0.2	0.32	
L1	0.05REF		

## **Recommended Pad outline**

